

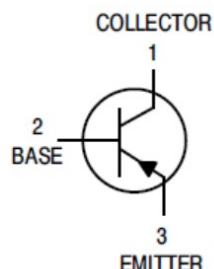
BC556

Features

- The PNP Bipolar Transistor is designed for use in linear and switching applications. The device is housed in the TO-92 package.
- These are PbFree Devices
- Complement to:BC546

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector- base voltage	BV_{CBO}	-80	V
Collector-emitter voltage	BV_{CEO}	-65	V
Emitter-base voltage	BV_{EBO}	-6	V
Collector current	I_{CM}	-100	mA
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector- Base Breakdown Voltage	BV_{CBO}	$I_C = -100\mu A, I_E = 0$	-80			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-65			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	-6			V
Collector- Base cut-off current	I_{CBO}	$V_{CB} = -70V, I_E = 0$			-0.1	μA
Collector-emitter cut-off current	I_{CEO}	$V_{CE} = -60V, I_B = 0$			-0.1	μA
Emitter-Base cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	H_{FE}	$V_{CE} = -5V, I_C = -2mA$	110		800	
Collector-emitter saturation voltage	V_{CESAT}	$I_C = -10mA, I_B = -0.5mA$		-90	-300	mV
		$I_C = -100mA, I_B = -5mA$		-250	-650	mV
Base-Emitter On Voltage	V_{BEON}	$V_{CE} = -5V, I_C = -2mA$	-600	660	-750	mV
		$V_{CE} = -5V, I_C = -10mA$			-800	mV
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1.0MHz$		3	6	pF
Noise Figure	N_F	$V_{CE} = -5V, I_C = -200\mu A$			10	dB

H_{FE} Classification

Classification	A	B	C
h_{FE}	110 ~ 220	200 ~ 450	420 ~ 800